**Guidelines for EDTM Paper**

**with 14-pt Title even for 2 Rows**

Hitoshi Wakabayashi1, Ken Uchida2, Shintaro Yamamichi3, Jiro Yugami4,

Wladyslaw Grabinski 5, and Shuji Ikeda6

1Tokyo Institute of Technology, Yokohama, Japan, [wakabayashi.h.ab@m.titech.ac.jp](mailto:wakabayashi.h.ab@m.titech.ac.jp)

2Keio University, 3IBM-Japan, 4Hitachi-Kokusai, 5MOS-AK, 6tei solutions

**Abstract**

This abstract is a brief (75 words) synopsis of your 2-page paper.

(Keywords: Manufacturing, CMOS and SOI)

**Introduction**

This template has been tailored for output on A4- or letter-sized paper. Margins, column widths, line spacing, and type styles are built-in; examples of the type styles are provided throughout this document and are identified in italic type, within parentheses, following the example, for the Electron Devices Technology and Manufacturing conference (EDTM) [1]. The extended 2-page paper consisting of 1 page of text with 2 columns and 1 page of figures and tables should be submitted by November 4th. Final camera ready 3-page manuscript should be sent by January 16th. However, due to the tight schedule of the inaugural EDTM 2017, we will consider the accepted 2-page initial extended-abstract as the final camera ready manuscript. If you do not submit the 3-page manuscript of your accepted 2-page extended-abstract by January 16, the initial extended-abstract would be published as it is. The paper should explain why/how it was done, principal results, and their significances.

**Formats and Fonts**

14, 12 and 11 pt of Times New Roman are used for the title, author/affiliation and text, respectively. In particular, the use of the International System of Units (SI Units) is advocated. And use a zero before decimal points: “0.25”, not “.25”.

*A. Equations*

11-pt Italic of Times New Roman is used for the equation, as shown in Eq. (1). The number of equation within parentheses are to position flush right.

*y = f(x)* (1)

*B. References*

When referring to them in the text, type the corresponding reference number in square brackets as shown at the end of this sentence [1].

*C. Table*

10.5 pt of Times New Roman is used for the caption, as shown in Table 1.

*D. Figure*

Note that the digest of EDTM will be provided as an electronic information through the USB. However, maximum 10 figures are recommended to find the achievements of your work. 10.5 pt of Times New Roman is also used for the caption.

**Conclusion**

Summarize the contents of paper. And finally, don't forget to check the spelling.

**Acknowledgments**

The authors gratefully acknowledge the contributions of T. Edison, G. Westinghouse, N. Tesla, A. Volta and A. Ampere to the electric power industry.

**References**

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Table 1: List of font sizes.

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| --- | --- | --- |
| Text | Type | Font [pt] |
| Title | Bold | 14 |
| Authors |  | 12 |
| Affiliation |  | 12 |
| Headings | Bold | 11 |
| *Sub-headings* | Italic | 11 |
| Main text |  | 11 |
| *Equation* | Italic | 11 |
| References |  | 10.5 |
| Footnotes |  | 10.5 |
| Table caption |  | 10.5 |
| Figure caption |  | 10.5 |







Fig. 1: Logos of the IEEE, EDS, and EDTM.Fig. 2: Direction to the Toyama International Conference Center from the Toyama station.

Fig. 3: The place of Toyama in Japan and expected nice mountain view from Toyama city during the EDTM.





Fig. 4: Outside photo of the Toyama International Conference Center.



Fig. 5: Window view from the Toyama International Conference Center.

Fig. 6: Main hall.